

器件

N 沟道 TO-220 封装

N-CHANNEL MOSFET in a TO-220 Plastic Package.

参数

$V_{DS} (V) = 60V$ $I_D = 120A$ ($V_{GS} = \pm 20V$)

$R_{DS(ON)} @ 10V \leq 6m\Omega$ (Typ. $4m\Omega$)

$R_{DS(ON)} @ 6V \leq 10m\Omega$ (Typ. $5m\Omega$)

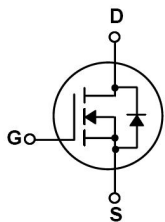
HF Product.

应用

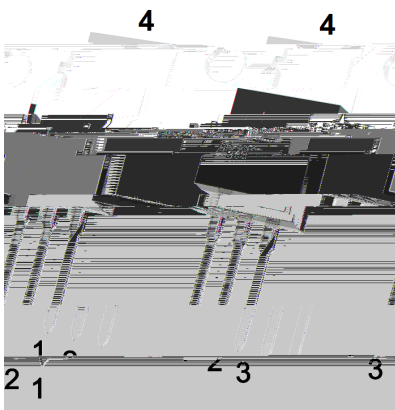
适用于 DC/DC 转换器和 UPS 逆变器

These devices are well suited for high efficiency switching DC/DC converters, Synchronous rectification and UPS inverter.

封装与引脚



封装与引脚



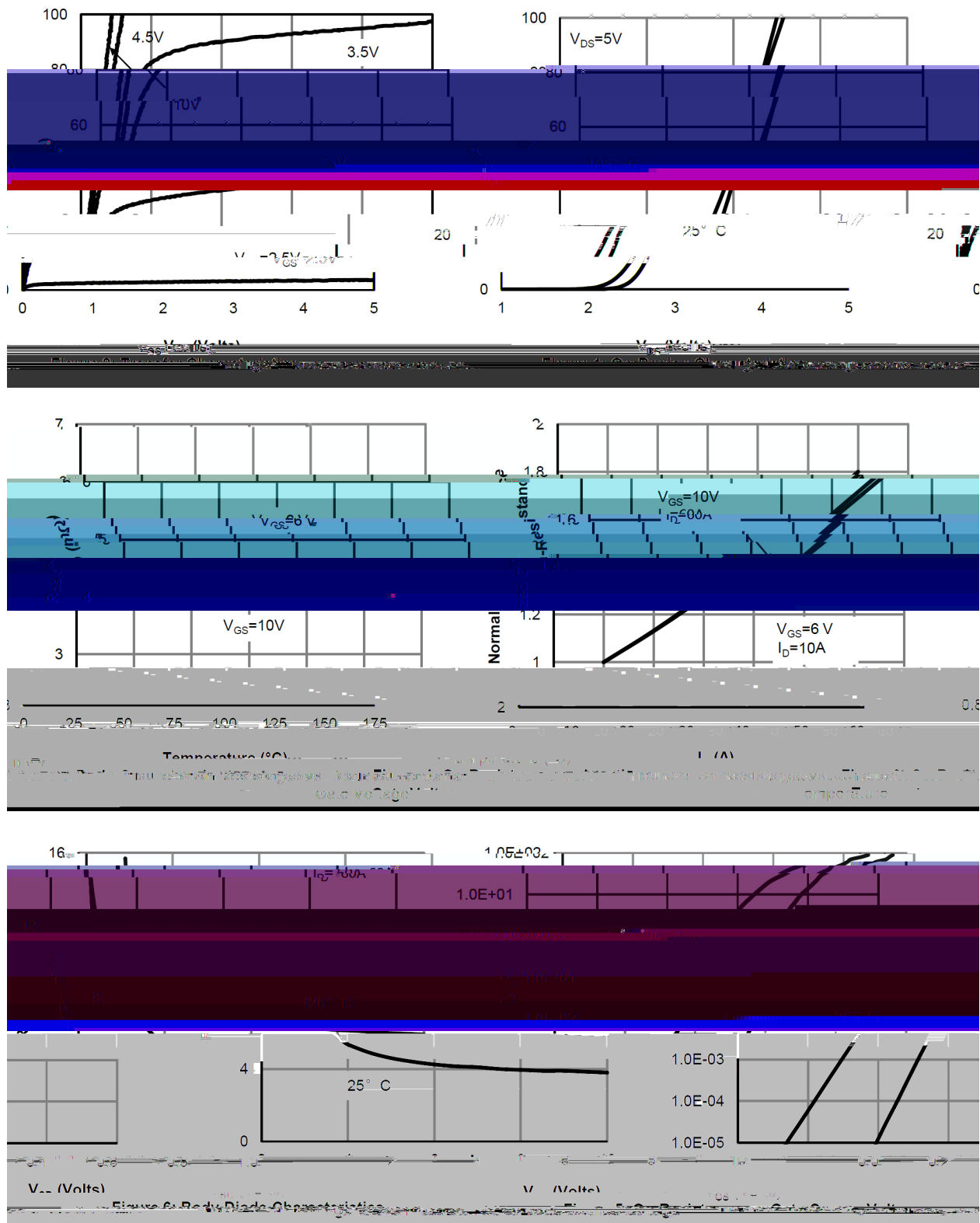
PIN1 G PIN 2 4 D PIN 3 S

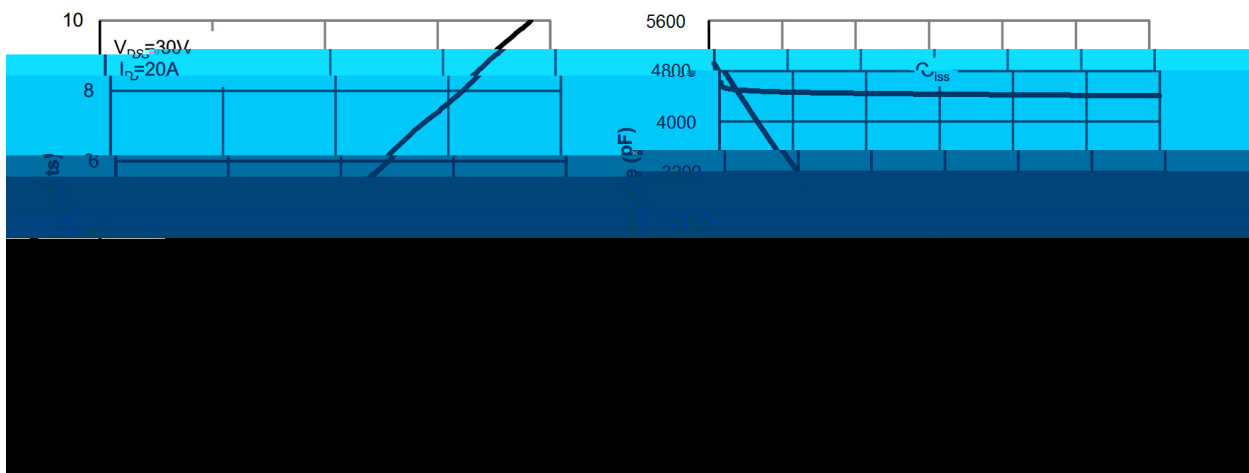
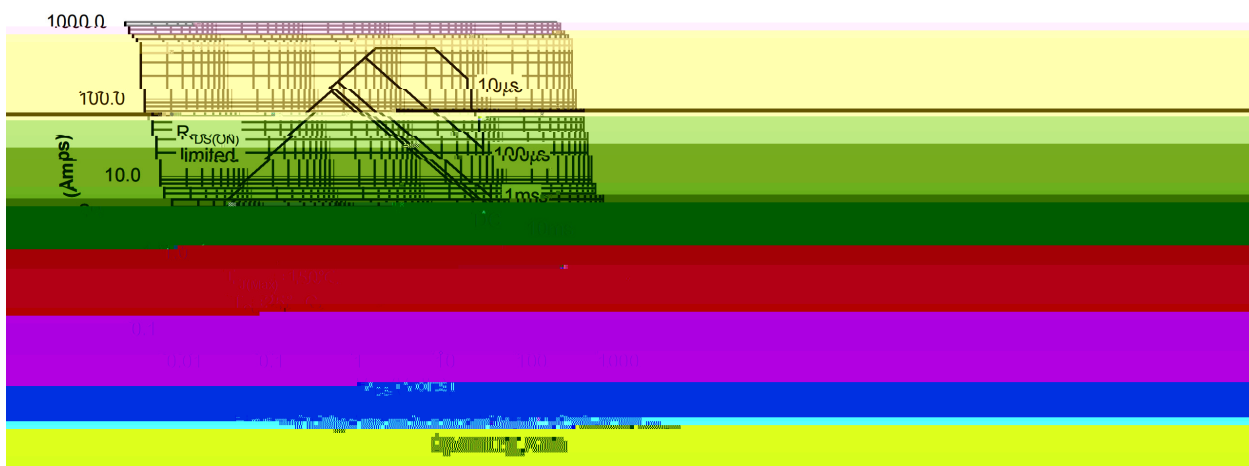
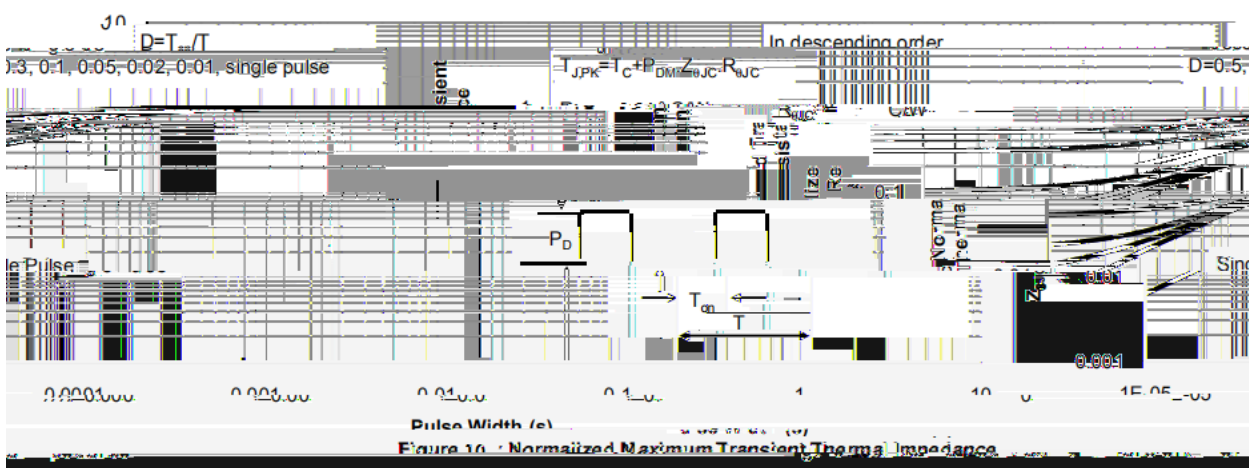
标识与封装

见

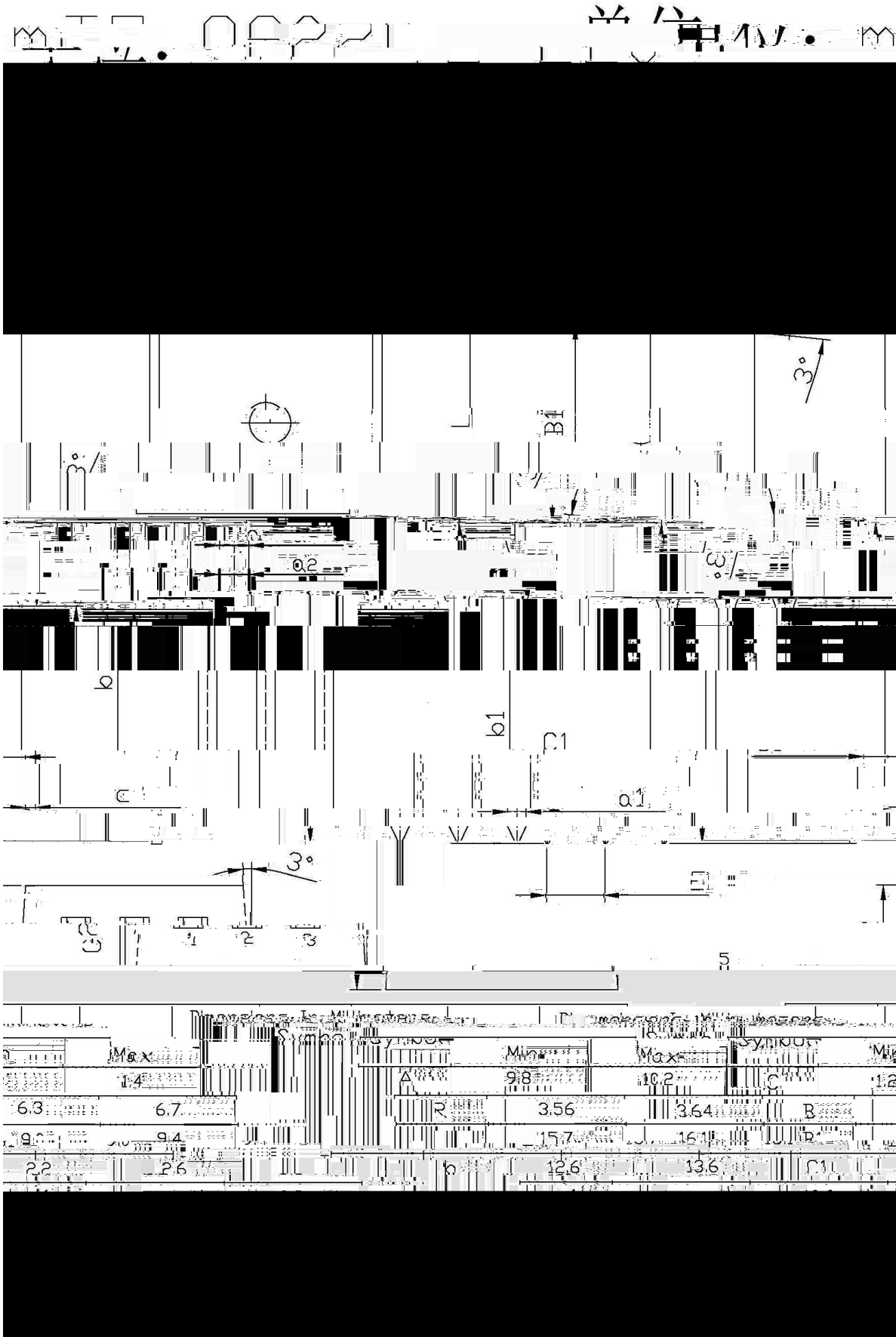
See Marking Instructions.

Figure 6: Body Diode Characteristics



$$= \exists \tilde{A} \exists E \vee f$$


U Ẹ Ồ Ẹ Ỗ Ỗ



↓ \$ 71 W'E V f 03

1. 25 150 60 90sec;
 2. 255±5 5±0.5sec;
 3. 2 10 /sec.

Note:

- 1.Preheating:25~150 , Time:60~90sec.
 2.Peak Temp.:255±5 , Duration:5±0.5sec.
 3. Cooling Speed: 2~10 /sec.

1 0 q - Y T

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

9 E <—

E / BULK

Package Type	Units					Dimension (unit mm ³)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box